Q.P. Code: 16EC401

R16

Reg. No:

SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR

(AUTONOMOUS)

B Tech II Year I Semester Supplementary Examinations Feb-2021

BASIC ELECTRONIC DEVICES

(Common to EEE & ECE)

Time: 3 hours

Max. Marks: 60

(Answer all Five Units $5 \times 12 = 60$ Marks)

UNIT-I

a What is PN Junction? Explain the formation of depletion layer in a PN junction.
b Discuss current components in a PN junction diode.

OR

2 a Derive the Diode Current Equation 6M

b Determine the value of forward current in the case of a PN junction diode, with $I_o = 6M 10\mu A$, $V_f = 0.8V$ at $T = 300^0 K$. Assume Silicon Diode.

UNIT-II

a Draw and explain the VI characteristics of a Zener Diode.

b Compare and contrast Zener diode and conventional PN Junction Diode. 4M

OR

4 a With neat diagram, describe the working principle and characteristics of UJT. 7M

b Explain the construction and applications of Solar Cell. 5M

UNIT-III

5 a Draw the circuit diagram of Full wave Center tap rectifier and explain its operation 6M with the help of waveforms.

b Derive the expressions for Ripple Factor and Efficiency of Full Wave Center tap **6M**

Rectifier.

OR

6 a Draw the circuit of capacitor filter and explain its operation. 5M

b Derive the expression for Ripple Factor of CLC Filter.

7M

UNIT-IV

7 a With neat diagram, explain the Input characteristics of a BJT in CE Configuration. 6M

b Derive the relation between α , β and Υ of a Transistor.

6M

OR

8 a Explain the construction and principle of operation of N-channel JFET. 7M

b Define the JFET Volt-Ampere Characteristics and determine FET parameters

5M

UNIT-V

9 a Mention different types of Biasing a Transistor. And explain the Fixed Bias of a 6M Transistor in detail.

b Define stability Factor of a Transistor and derive the expression for it.

6M

OR

10 a Describe Thermistor and Sensistor Compensation Techniques.

6M

b Discuss about Thermal Runaway and Thermal Resistance.

6M

*** END ***